

Abstract of the Disclosure

A method for manufacturing a GaN compound semiconductor light emitting device is provided. In the method for manufacturing a light emitting device including at least one layer of a p-type compound semiconductor layer on an active layer where light is generated and a p-type electrode on the p-type compound semiconductor layer, after forming the p-type compound semiconductor layer on the active layer, the resultant structure is annealed twice, and the p-type electrode is formed on the annealed p-type compound semiconductor layer. As a result of the annealing performed twice, the resistance of the p-GaN layer is lowered, contact resistance between the p-GaN layer and the p-type electrode is lowered even when the p-type electrode is formed as a single metal layer, and thus, the driving voltage of the light emitting device is lowered. When using the method, a p-type electrode of a light emitting device can be manufactured from various kinds of materials by applying various techniques.